

## TMT4320 Nanomaterials, fall 2015

## **EXERCISE 11**

**Guidance:** 

Thursday 11<sup>th</sup> November, 18:15-20:00, H3 Friday 13<sup>th</sup> November, 14:00, boxes outside R7 or on It's learning **Due date:** 

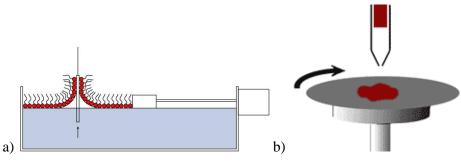
## **PROBLEM 1**

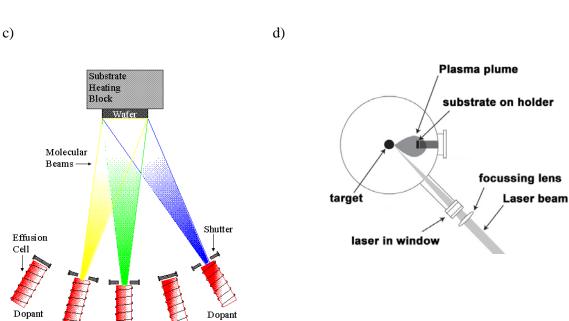
Gallium

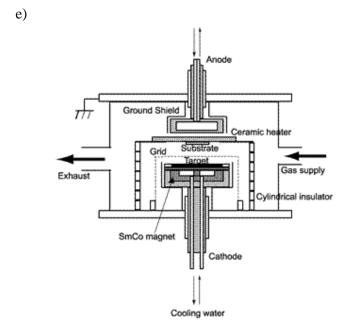
Aluminum

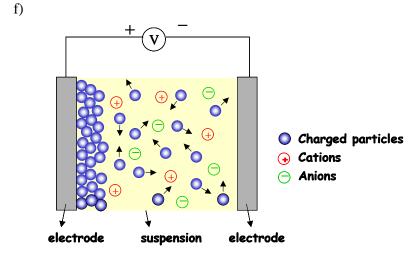
Arsenic

The figures below illustrate various methods to produce thin films on a substrate. For each figure; name the method, describe the method briefly, and state if the method is a wetchemical deposition method, chemical vapor deposition method or physical vapor deposition method.









## **PROBLEM 2**

If you were to produce the following thin films and nanostructures, which thin film deposition/growth method would you prefer to use (is possible and best to use)? Give a short explanation of your choice.

- a) An InP<sub>0.85</sub>Sb<sub>0.15</sub>/GaAs multilayer structure on an InP substrate
- b) A monolayer of hexadecanethiol ( $C_{16}H_{33}SH$ ) on a gold substrate
- c) A 10 nm thick PbTiO<sub>3</sub> film on a SrTiO<sub>3</sub> substrate